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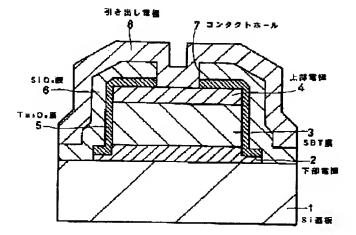
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TITLE

: DIELECTRIC CAPACITOR AND

MANUFACTURE THEREOF



ABSTRACT: PROBLEM TO BE SOLVED: To provide a dielectric capacitor with which the deterioration in characteristics due to the reaction between the ferrodielectric film of the dielectric capacitor and an interlayer insulating film and due to the oxygen defect of the dielectric film of the dielectric capacitor or the ferrodielectric film, and to provide a method of manufacturing the above-mentioned dielectric capacitor.

> SOLUTION: A lower electrode 2, an SBT film 3 and an upper electrode 4 are successively formed on a conductive Si substrate 1, this dielectric capacitor is covered by Ta<sub>2</sub>O<sub>5</sub>, and its surface is covered by an SiO<sub>2</sub> film 6. A contact hole 7 is provided above the upper electrode 4 on the Ta<sub>2</sub>O<sub>5</sub> film 5 and the SiO<sub>2</sub> film 6. A lead-out electrode 8 is provided in such a manner that it is connected with the upper electrode 4 through the contact hole 7. The surface of the Ta<sub>2</sub>O<sub>5</sub> film 5 may be covered by an insulating SiN film having hydrogen diffusion preventing effect.

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